



Chip Termination 150 Watts, 50Ω



Features:

- RoHS Compliant
- 150 Watts
- DC 3.0 GHz
- **AIN Ceramic** •
- **Non-Nichrome Resistive** Element
- Low VSWR .
- 100% Tested

Description:

The A150N50X4E is high performance Aluminum Nitride (AlN) chip termination intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators and for use in power combiners. The termination is also RoHS compliant!

General Specifications:

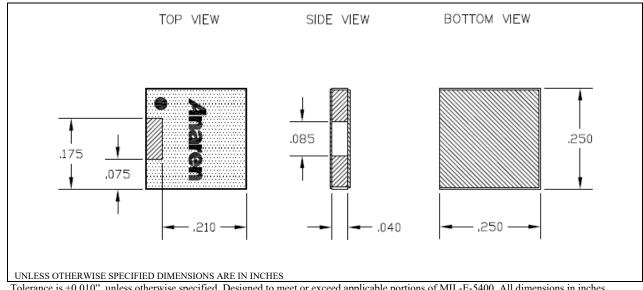
Resistive Element	Thick film
Substrate	AIN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-50 to +200°C (see de rating chart)

Electrical Specifications:

Resistive Value:	50 Ohms, ± 2%
Power:	150 Watts
Frequency Range:	DC – 3.0 GHz
Return Loss	25dB DC – 2.0 GHz
	20dB DC – 3.0 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. Specifications subject to change.

Outline Drawing:



Tolerance is ±0.010", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.

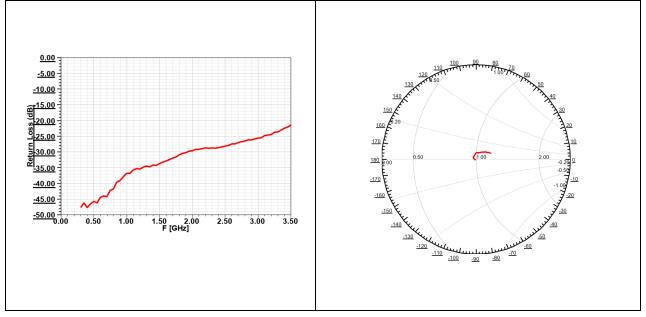


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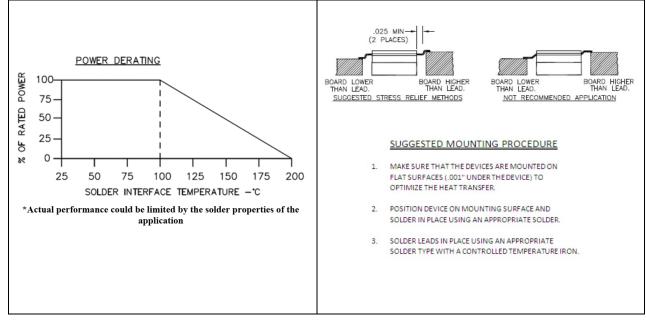


Typical Performance:



Power de-rating:

Mounting Footprint:



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